

CLAIM AMENDMENTS

1. (Previously Presented) A method comprising:
soaking a substrate having a dielectric deposited thereon in a salt solution,
said dielectric having a first dielectric constant;
depositing an oxide on said dielectric, said oxide having a second dielectric
constant different from the first dielectric constant; and
adjusting the pH of the salt solution.
2. (Previously Presented) The method of claim 1 wherein depositing an oxide
on said dielectric includes depositing primarily aluminum oxide on said dielectric.
3. (Original) The method of claim 1 wherein soaking said substrate in said salt
solution includes soaking said substrate in a salt solution comprising an aluminum salt.
4. (Original) The method of 3 wherein soaking said substrate in said salt
solution comprising said aluminum salt includes soaking said substrate in a salt solution
comprising aluminum chloride dissolved in water.
5. (Original) The method of 3 wherein soaking said substrate in said salt
solution comprising said aluminum salt includes soaking said substrate in a salt solution
comprising aluminum nitrate dissolved in water.
6. (Original) The method of claim 3 wherein soaking said substrate in said salt
solution comprising said aluminum salt includes causing the reactants in said aluminum
salt solution available for surface reaction to range from about a few parts per million to
about one percent.

Claim 7 (Canceled)

8. (Original) The method of claim 1 wherein depositing said oxide on said dielectric includes depositing said oxide on silicon dioxide.
9. (Original) The method of claim 1 wherein depositing said oxide on said dielectric includes depositing said oxide on hafnium oxide.
10. (Original) The method of claim 1 including depositing a gate material on said oxide.
11. (Previously Presented) A method comprising:
exposing a dielectric deposited on a substrate to a salt solution; and
causing an oxide which is different from said dielectric to form on said dielectric, at least a portion of said dielectric to remain between said substrate and said oxide as part of a functional structure.
12. (Previously Presented) The method of claim 11 including exposing said dielectric on said substrate to an aluminum salt solution.
13. (Previously Presented) The method of claim 12 including exposing said dielectric on said substrate to an aluminum chloride solution.
14. (Previously Presented) The method of claim 12 including exposing said dielectric on said substrate to an aluminum nitrate solution.
15. (Previously Presented) The method of claim 12 including adjusting the pH of said aluminum salt solution.

16. (Original) The method of claim 12 wherein causing an oxide to deposit on said dielectric includes causing reactants in said aluminum salt solution to react with the top surface of said dielectric.

17. (Original) The method of claim 16 wherein causing said reactants in said aluminum salt solution to react with the top surface of said dielectric includes depositing an aluminum oxide layer ranging in thickness from about a few parts per million to one or more atomic layers.

18. (Original) The method of claim 11 wherein exposing said dielectric to said salt solution includes exposing a dielectric selected from the group consisting of silicon dioxide, hafnium dioxide and zirconia to said salt solution.

19. (Original) The method of claim 11 including removing said substrate from said salt solution and rinsing.

20. (Original) The method of claim 11 wherein exposing said dielectric to said salt solution includes exposing said dielectric to said salt solution for about a few seconds to about an hour.

21. (Currently Amended) A method comprising:
depositing a dielectric on a substrate using a first method of deposition, said dielectric being an oxide; and
depositing an oxide on said dielectric by immersing said substrate in a an aluminum salt solution, the top surface of said dielectric to react with said aluminum salt solution, said deposition by immersing different from said first method of deposition.

Claim 22 (Canceled)

23. (Original) The method of claim 22 wherein depositing said oxide on said substrate includes depositing hafnium oxide on said substrate.

24. (Original) The method of claim 22 wherein depositing said oxide on said substrate includes depositing zirconia on said substrate.

25. (Original) The method of claim 22 wherein depositing said oxide on said substrate includes depositing silicon dioxide on said substrate.

26. (Canceled).

27. (Currently Amended) The method of claim ~~[[26]]~~ 21 wherein causing said aluminum oxide to deposit on said dielectric includes causing about a few parts per million of aluminum oxide to one or more atomic layers of aluminum oxide to deposit on said dielectric.

28. (Currently Amended) The method of claim ~~[[26]]~~ 21 including adjusting the pH of said aluminum salt solution.

29. (Canceled).

30. (Previously Presented) The method of claim 21 including forming a gate material on said oxide.

31. (Previously Presented) The method of claim 21 wherein depositing a dielectric on a substrate includes using a chemical vapor deposition technique to deposit said dielectric.

Claims 32-35 (Canceled)

36. (New) A method comprising:
exposing a dielectric deposited on a substrate to a salt solution, the salt solution to react with an exposed surface of said dielectric to form an oxide on said dielectric that is different from said dielectric; and
forming another layer over said dielectric and said oxide, at least a portion of said dielectric, oxide, and another layer part of a semiconductor device after processing is complete.

37. (New) The method of claim 36 wherein forming another layer includes forming a layer of a gate material.

38. (New) The method of claim 36 wherein exposing a dielectric to a salt solution includes exposing said dielectric to an aluminum salt solution.

39. (New) The method of claim 36 wherein exposing a dielectric includes exposing one of hafnium oxide, silicon dioxide, or zirconia.

40. (New) The method of claim 36 wherein exposing a dielectric includes exposing a dielectric to a pH adjusted salt solution.